

YJ Planar Schottky Barrier Diode Die Specification

40V 0.04A,9mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB009L040AG-155A

Main Products Characteristics

- Average forward current: IF(AV) = 0.04A
- Maximum operating junction temperature: Tj = 125 °C
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL/3.915um

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

IF =0.04A
Pulse Test: tp = 800 μs, δ ≤ 2%

Device Schematics and Outline Drawing

- Die Thickness *
- Die Size **
- Top Metal Pad
- Active Area
- Top Metal
- Back Metal
- Steet width

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.
Recommended Storage Environment:
does not guarantee device performance after assembly.